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ON Semiconductor MBR120ESFT1

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Distributor of ON Semiconductor: Excellent Integrated System Limited Datasheet of MBR120ESFT1 - DIODE SCHOTTKY 20V 1A SOD123L Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

MBR120ESFT1

Surface Mount Schottky Power Rectifier

Plastic SOD-123 Package

This device uses the Schottky Barrier principle with a large area metal-to-silicon power diode. Ideally suited for low voltage, high frequency rectification or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. This package also provides an easy to work with alternative to leadless 34 package style. Because of its small size, it is ideal for use in portable and battery powered products such as cellular and cordless phones, chargers, notebook computers, printers, PDAs and PCMCIA cards. Typical applications are AC-DC and DC-DC converters, reverse battery protection, and "Oring" of multiple supply voltages and any other application where performance and size are critical.

Features

- Guardring for Stress Protection
- Low Leakage
- 150°C Operating Junction Temperature
- Epoxy Meets UL 94 V–0 @ 0.125 in
- Package Designed for Optimal Automated Board Assembly
- ESD Ratings: Machine Model, C
 - Human Body Model, 3B
- Pb–Free Packages are Available

Mechanical Characteristics

- Reel Options: MBR120ESFT1 = 3,000 per 7" reel/8 mm tape MBR120ESFT3 = 10,000 per 13" reel/8 mm tape
- Device Marking: L2E
- Polarity Designator: Cathode Band
- Weight: 11.7 mg (approximately)
- Case: Epoxy, Molded
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



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SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES 20 VOLTS



SOD-123FL CASE 498 PLASTIC

MARKING DIAGRAM



L2E = Specific Device Code M = Date Code Pb-Free Package (Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]	
MBR120ESFT1	SOD-123FL	3000/Tape & Reel	
MBR120ESFT1G	SOD-123FL (Pb-Free)	3000/Tape & Reel	
MBR120ESFT3	SOD-123FL	10000/Tape & Reel	
MBR120ESFT3G	SOD-123FL (Pb-Free)	10000/Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



MBR120ESFT1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	20	V	
Average Rectified Forward Current (At Rated V_R , T_L = 140°C)	Ι _Ο	1.0	А	
Peak Repetitive Forward Current (At Rated V _R , Square Wave, 20 kHz, T _L = 125°C)	I _{FRM}	2.0	A	
Non-Repetitive Peak Surge Current (Non-Repetitive peak surge current, halfwave, single phase, 60 Hz)	I _{FSM}	40	A	
Storage Temperature	T _{stg}	-65 to 150	°C	
Operating Junction Temperature	TJ	-65 to 150	°C	
Voltage Rate of Change (Rated V_R , $T_J = 25^{\circ}C$)	dv/dt	10,000	V/µs	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance – Junction-to-Lead (Note 1)	R _{til}	26	°C/W
Thermal Resistance – Junction–to–Lead (Note 2)	R _{til}	21	
Thermal Resistance – Junction-to-Ambient (Note 1)	R _{tja}	325	
Thermal Resistance – Junction-to-Ambient (Note 2)	R _{tja}	82	

1. Mounted with minimum recommended pad size, PC Board FR4.

2. Mounted with 1 in. copper pad (Cu area 700 mm²).

ELECTRICAL CHARACTERISTICS

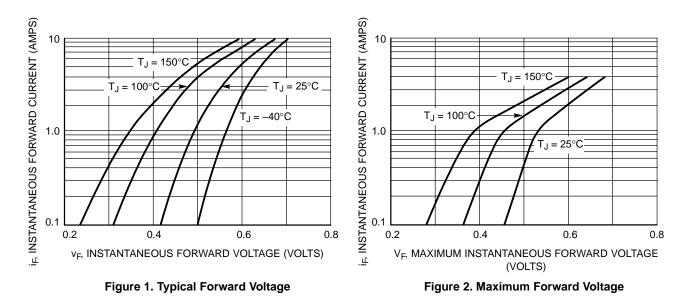
Maximum Instantaneous Forward Voltage (Note 3), See Figure 2	V _F	T _J = 25°C	$T_J = 100^{\circ}C$	V
$(I_F = 0.1 \text{ A})$ $(I_F = 1.0 \text{ A})$ $(I_F = 2.0 \text{ A})$		0.455 0.530 0.595	0.360 0.455 0.540	
Maximum Instantaneous Reverse Current (Note 3), See Figure 4	I _R	T _J = 25°C	T _J = 100°C	μΑ
(V _R = 20 V) (V _R = 10 V) (V _R = 5.0 V)		10 1.0 0.5	1600 500 300	

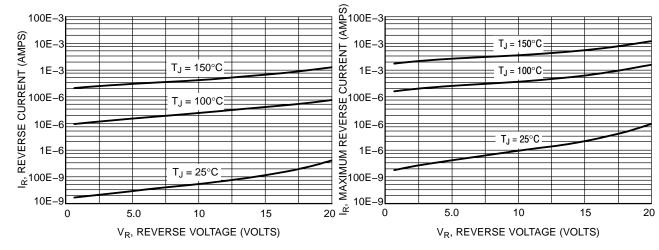
3. Pulse Test: Pulse Width \leq 250 $\mu s,$ Duty Cycle \leq 2%.



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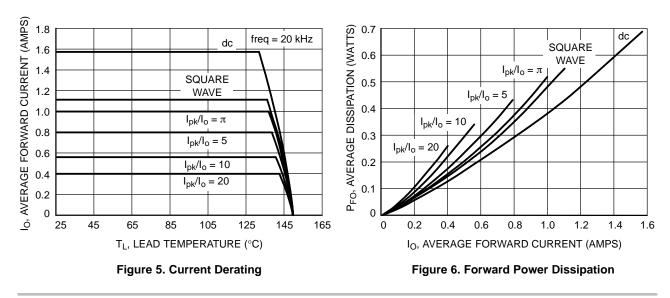
MBR120ESFT1







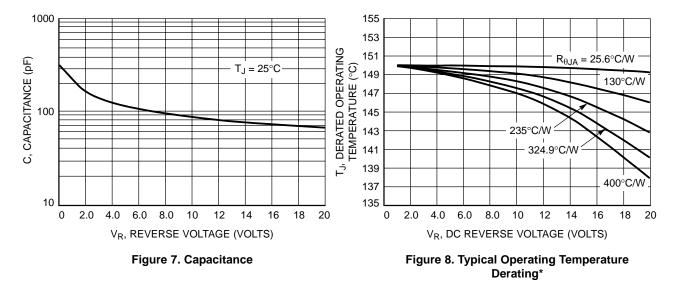






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* Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation: $T_J = T_{Jmax} - r(t)(Pf + Pr)$ where

- r(t) = thermal impedance under given conditions,
- Pf = forward power dissipation, and
- Pr = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = Rthja. For other power applications further calculations must be performed.

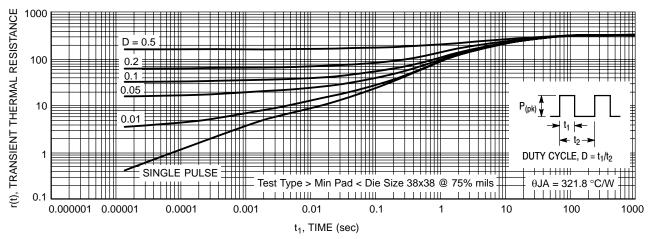


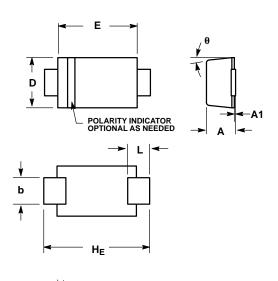
Figure 9. Thermal Response



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PACKAGE DIMENSIONS

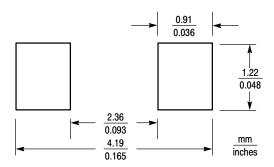
SOD-123LF CASE 498-01 **ISSUE A**



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH. 4. DIMENSIONS D AND J ARE TO BE MEASURED ON FLAT SECTION OF THE LEAD: BETWEEN 0.10 AND 0.25 MM FROM THE LEAD TIP.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	0.95	1.00	0.035	0.037	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
q	0.70	0.90	1.10	0.028	0.035	0.043
c	0.10	0.15	0.20	0.004	0.006	0.008
D	1.50	1.65	1.80	0.059	0.065	0.071
Е	2.50	2.70	2.90	0.098	0.106	0.114
L	0.55	0.75	0.95	0.022	0.030	0.037
HE	3.40	3.60	3.80	0.134	0.142	0.150
θ	0°	-	8°	0°	-	8°

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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